Listing of the Claims

1. (Currently Amended) A liquid crystal display device comprising:

a substrate;

a thin film transistor including a gate electrode, a source electrode, and a drain electrode on the substrate;

a pixel electrode electrically connected to the drain electrode and in direct contact with the substrate;

a data line electrically connected with the source electrode;

a first insulating layer, a pure amorphous silicon layer, and a doped amorphous silicon layer sequentially layered under the data line;

a data pad at one end of the data line;

a gate line electrically connected with the gate electrode; and

a gate pad electrode at one end of the gate line,

wherein the gate pad electrode is formed of a same material and in a same layer as the pixel electrode in a single layer in direct contact over the first insulating layer,

wherein the first insulating layer includes an opening that exposes a portion of the gate pad ~~line~~, and

wherein the gate pad electrode electrically contacts the exposed portion of the gate pad ~~line~~ and overlaps the first insulating layer.

2. (Original) The device of claim 1, wherein the pixel electrode is selected from a group consisting of indium tin oxide (ITO) and indium zinc oxide (IZO).

3. (Currently Amended) A liquid crystal display device comprising:

a substrate;

a thin film transistor including a gate electrode, a source electrode, and a drain electrode on the substrate;

a pixel electrode electrically connected to the drain electrode;

a data line electrically connected with the source electrode;

a first insulating layer, a pure amorphous silicon layer, and a doped amorphous silicon layer sequentially layered under the data line;

a data pad at one end of the data line;

a gate line electrically connected with the gate electrode; and

a gate pad electrode at one end of the gate line,

wherein the gate pad electrode is formed directly on top of the first insulating layer,

wherein the first insulating layer includes an opening that exposes a portion of the gate pad ~~line~~,

wherein the gate pad electrode electrically contacts the exposed portion of the gate pad ~~line~~ and overlaps the first insulating layer,

wherein the drain electrode has a through hole that exposes a portion of the first insulating layer, and wherein the pixel electrode electrically contacts an inner side surface of the drain electrode via the through hole.

4. (Currently Amended) A liquid crystal display device comprising:

a substrate;

a thin film transistor including a gate electrode, a source electrode, and a drain electrode on the substrate;

a pixel electrode electrically connected to the drain electrode;

a data line electrically connected with the source electrode;

a first insulating layer, a pure amorphous silicon layer, and a doped amorphous silicon layer sequentially layered under the data line;

a data pad at one end of the data line;

a gate line electrically connected with the gate electrode;

a gate pad electrode at one end of the gate line; and

a data pad electrode, wherein the data pad has a data pad contact hole passing through the doped amorphous silicon layer and through the amorphous silicon layer, wherein the data pad electrode electrically contacts an inner side surface of the data pad via the data pad contact hole,

wherein the gate pad electrode is formed directly on top of the first insulating layer, wherein the first insulating layer includes an opening that exposes a portion of the gate pad ~~line~~, and

wherein the gate pad electrode electrically contacts the exposed portion of the gate pad ~~line~~ and overlaps the first insulating layer.

5. (Original) The device of claim 4, wherein said data pad electrode is comprised of the same material as said pixel electrode.

Claims 6-20 (Canceled)

21. (Previously Presented) The device of claim 3, wherein the pixel electrode is selected from a group consisting of indium tin oxide (ITO) and indium zinc oxide (IZO).

22. (Previously Presented) The device of claim 4, wherein the pixel electrode is selected from a group consisting of indium tin oxide (ITO) and indium zinc oxide (IZO).